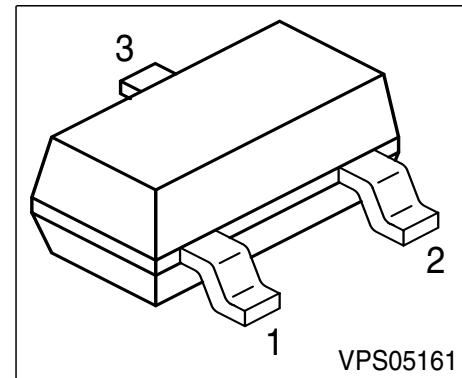
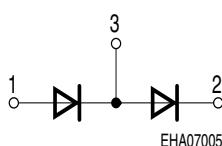
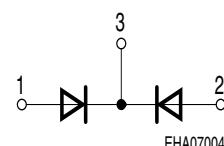
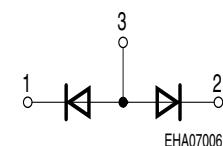


Silicon Schottky Diodes

- For low-loss, fast-recovery, meter protection, bias isolation and clamping applications
- Integrated diffused guard ring
- Low forward voltage

**BAT 64****BAT 64-04****BAT 64-05****BAT 64-06**

ESD: Electrostatic discharge sensitive device, observe handling precaution!

| Type | Marking | Pin Configuration | | | Package |
|-----------|---------|-------------------|--------|-----------|---------|
| BAT 64 | 63s | 1 = A | 2 n.c. | 3 = C | SOT-23 |
| BAT 64-04 | 64s | 1 = A1 | 2 = C2 | 3 = C1/A2 | SOT-23 |
| BAT 64-05 | 65s | 1 = A1 | 2 = A2 | 3 = C1/2 | SOT-23 |
| BAT 64-06 | 66s | 1 = C1 | 2 = C2 | 3 = A1/2 | SOT-23 |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|-----------|-------------|------------|
| Diode reverse voltage | V_R | 40 | V |
| Forward current | I_F | 250 | mA |
| Average forward current (50/60Hz, sinus) | I_{FAV} | 120 | |
| Surge forward current ($t \leq 10ms$) | I_{FSM} | 800 | |
| Total power dissipation, $T_S = 61^\circ C$ | P_{tot} | 250 | mW |
| Junction temperature | T_j | 150 | $^\circ C$ |
| Storage temperature | T_{stg} | -55 ... 150 | |

Maximum Ratings

| | | | |
|----------------------------|------------|------------|-----|
| Junction - ambient 1) | R_{thJA} | ≤ 495 | K/W |
| Junction - soldering point | R_{thJS} | ≤ 355 | |

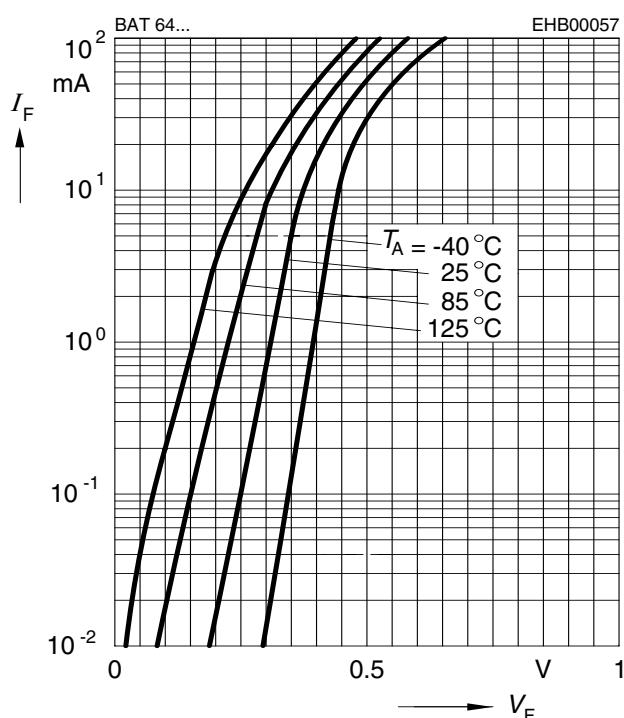
1) Package mounted on epoxy pcb 40mm x 40mm x 1.5mm / 0.5cm² Cu

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

| Parameter | Symbol | Values | | | Unit |
|---|--------|--------|--------------------------|--------------------------|---------------|
| | | min. | typ. | max. | |
| DC characteristics | | | | | |
| Reverse current $V_R = 25 \text{ V}$ | I_R | - | - | 2 | μA |
| Reverse current $V_R = 25 \text{ V}, T_A = 150^\circ\text{C}$ | I_R | - | - | 200 | μA |
| Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 30 \text{ mA}$ $I_F = 100 \text{ mA}$ | V_F | - | 320 385 440 570 | 350 430 520 750 | mV |
| AC characteristics | | | | | |
| Diode capacitance $V_R = 1 \text{ V}, f = 1 \text{ MHz}$ | C_T | - | 4 | 6 | pF |

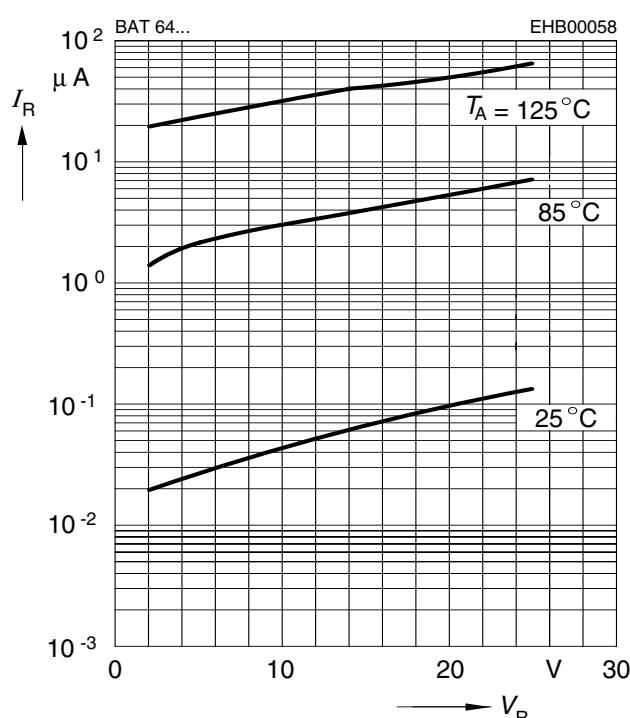
Forward current $I_F = f(V_F)$

$T_A = \text{Parameter}$



Reverse current $I_R = f(V_R)$

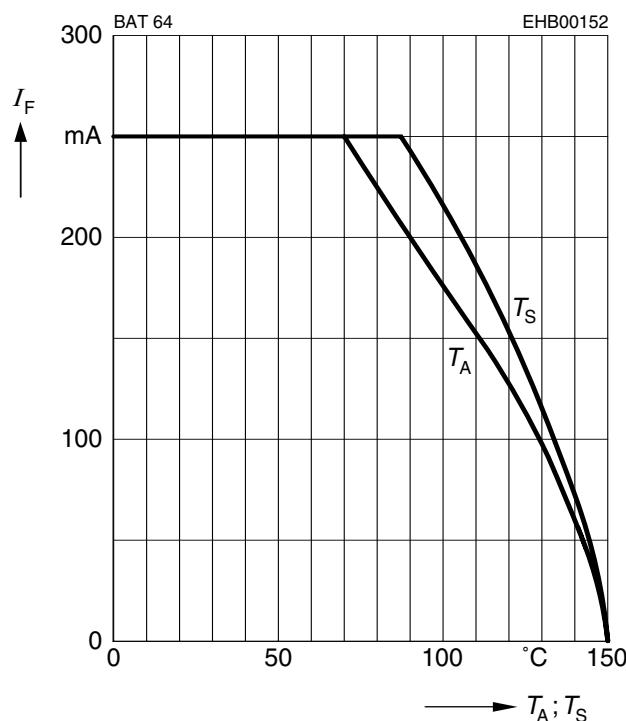
$T_A = \text{Parameter}$



Forward current $I_F = f(T_A^*; T_S)$

*Package mounted on epoxy

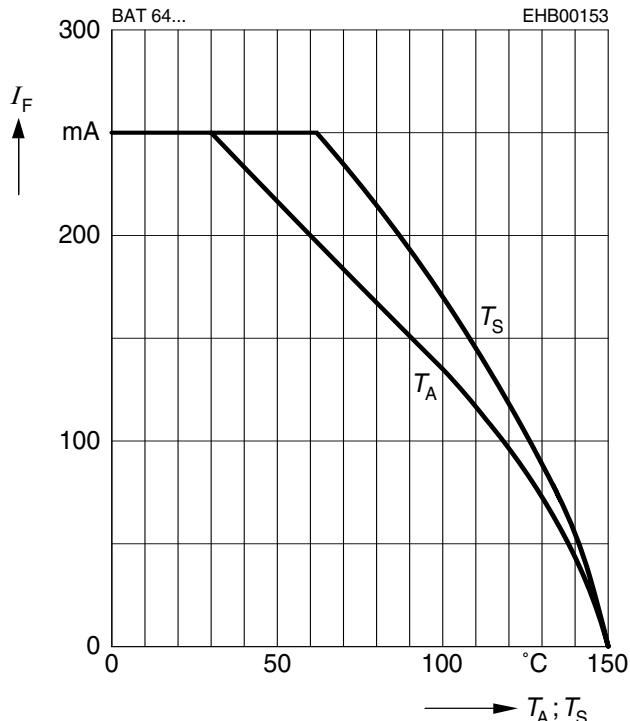
BAT 64



Forward current $I_F = f(T_A^*; T_S)$

*Package mounted on epoxy

BAT 64-04... (I_F per Diode)



Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$

